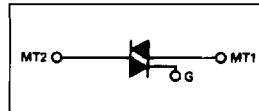


Sensitive Gate Triacs

Silicon Bidirectional Triode Thyristors

... designed primarily for ac power switching. The gate sensitivity of these triacs permits the use of economical transistorized or integrated circuit control circuits, and it enhances their use in low-power phase control and load-switching applications.

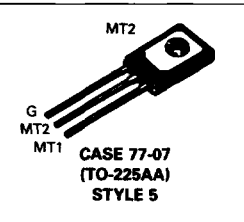
- Very High Gate Sensitivity
- Low On-State Voltage at High Current Levels
- Glass-Passivated Chip for Stability
- Small, Rugged Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability



T2322*
T2323*
Series*

*Motorola preferred devices

SENSITIVE GATE TRIACs
2.5 AMPERES RMS
200 thru 600 VOLTS



MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Suffix	Symbol	Value	Unit
Peak Repetitive Off-State Voltage, Note 1 ($T_J = 25$ to 100°C , Gate Open) T2322, T2323	B	V_{DRM}	200	Volts
	D		400	
	M		600	
RMS On-State Current ($T_C = 70^\circ\text{C}$) (Full-Cycle Sine Wave 50 to 60 Hz)		$I_T(\text{RMS})$	2.5	Amps
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz)		I_{TSM}	25	Amps
Circuit Fusing ($t = 8.3$ ms)		i^2t	2.6	A^2s
Peak Gate Power (1 μs)		P_{GM}	10	Watts
Average Gate Power ($T_C = 60^\circ\text{C} + 38.3$ ms)		$P_{G(AV)}$	0.15	Watt
Peak Gate Current (1 μs)		I_{GM}	0.5	Amp
Operating Junction Temperature Range		T_J	-40 to +110	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-40 to +150	$^\circ\text{C}$
Mounting Torque (6-32 Screw), Note 2		—	8	in. lb.

Note 1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Note 2. Torque rating applies with use of torque washer (Shakeproof WD19523 or equivalent). Mounting Torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Main terminal 2 and heat-sink contact pad are common.

For soldering purposes (either terminal connection or device mounting), soldering temperatures shall not exceed $+200^\circ\text{C}$, for 10 seconds. Consult factory for lead bending options.

T2322 • T2323 Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.5	$^{\circ}C/W$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ and either polarity of MT2 to MT1 voltage unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Blocking Current ($V_D = \text{Rated } V_{DRM}$, Gate Open) $T_J = 25^{\circ}C$ $T_J = 100^{\circ}C$	I_{DRM}	— —	— 0.2	10 0.75	μA mA
Peak On-State Voltage* ($I_{TM} = 10 A$) T2323 Series T2322 Series	V_{TM}	— —	1.7 1.7	2.6 2.2	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 V$, $R_L = 30 \Omega$) All Modes MT2(+), G(+); MT2(-), G(-) T2322 Series MT2(+), G(+); MT2(-), G(-) T2323 Series MT2(+), G(-); MT2(-), I G(+) T2323 Series	I_{GT}	— — —	— — —	10 25 40	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 V_{dc}$, $R_L = 30 \Omega$, $T_C = 25^{\circ}C$) ($V_D = V_{DRM}$, $R_L = 125 \Omega$, $T_C = 100^{\circ}C$)	V_{GT}	— 0.15	1 —	2.2 —	Volts
Holding Current ($V_D = 12 V$, $I_{TM} = 150 mA$, Gate Open)	I_H	—	15	30	mA
Gate Controlled Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 10 A$ pk, $I_G = 60 mA$)	t_{gt}	—	1.8	2.5	μs
Critical Rate-of-Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Waveform, $T_C = 100^{\circ}C$)	dv/dt	10	100	—	$V/\mu s$
Critical Rate-of-Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 3.5 A$ pk, Commutating $di/dt = 1.26 A/ms$, Gate Unenergized, $T_C = 90^{\circ}C$)	$dv/dt(c)$	1	4	—	$V/\mu s$

*Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.

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